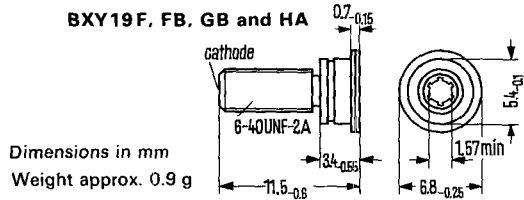


# BXY19F, BXY19FB, BXY19GB, BXY19HA

## Charge storage varactors for frequency multiplication

Type	Order number
BXY19F	Q60223-Y19-F
BXY19FB	Q62702-X53
BXY19GB	Q60223-Y19-G2
BXY19HA	Q62702-X50



	BXY 19 F	BXY 19 FB	BXY 19 GB	BXY 19 HA	
Frequency range	0.1 to 3	0.1 to 3	0.1 to 2.4	0.1 to 2.0	GHz
Input power	to 15	to 15	to 20	to 30	W
Junction temperature	+150	+150	+150	+150	°C
Storage temperature	-55 to +175	-55 to +175	-55 to +175	-55 to +175	°C
Thermal resistance Junction to case	$\leq 12$	$\leq 12$	$\leq 10$	$\leq 10$	K/W
Diode capacitance ( $V_R = 0$ V; $f = 1$ MHz)	9 to 18	12 to 18	20 to 30	30 to 40	pf
Breakdown voltage ( $I_R = 10$ $\mu$ A)	85 to 105	85 to 105	95 to 115	115 to 135	V
Reverse current ( $V_R = 30$ V)	$\leq 5$	$\leq 5$	$\leq 5$	$\leq 5$	nA
Forward voltage ( $I_F = 100$ mA)	$\leq 1.0$	$\leq 1.0$	$\leq 1.0$	$\leq 1.0$	V
Series resistance ( $V_R = 20$ V; $f = 2.4$ GHz)	$\leq 0.5$	$\leq 0.5$	$\leq 0.5$	$\leq 0.5$	$\Omega$
Storage time ( $I_F =$ 100 mA; $I_R = 200$ mA) fall to 80% of $I_R$	90	90	150	180	ns
Fatt time ( $I_F =$ 100 mA; $I_R = 200$ mA) fall from 80% to 20% of $I_R$	2	2	4	5	ns
Case capacitance (without grub screw)	1.0	1.0	1.0	1.0	pf
Case series inductance (without grub screw)	0.6	0.6	0.6	0.6	nH
Applications: conversion loss, e.g. tripling or doubling from	3.5	3.0	1.5	1.5	db
to	0.8	0.8	0.4	0.2	GHz
RF input power	2.4	2.4	0.8	0.4	GHz
	10	10	15	20	W